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(54) **SOI SUBSTRATE AND RELATED METHODS**

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H01L 23/12 (2006.01)
H01L 23/34 (2006.01)
H01L 23/522 (2006.01)

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(58) **Field of Classification Search**

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See application file for complete search history.

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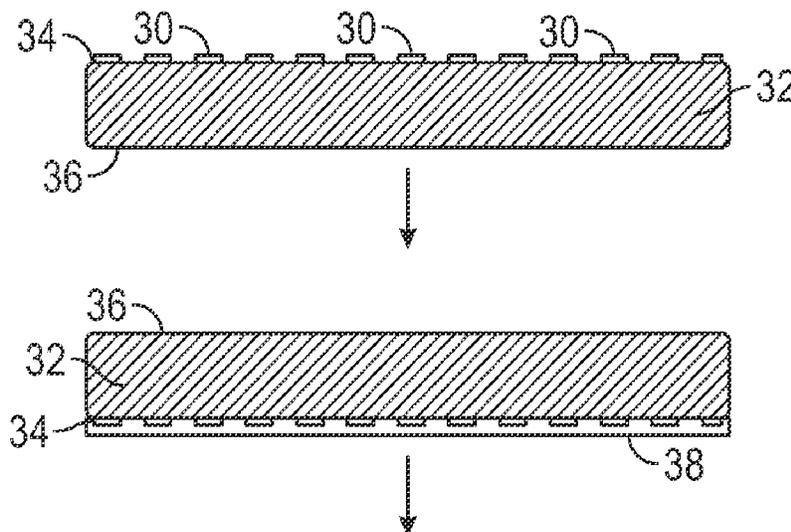
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(57) **ABSTRACT**

Implementations of a silicon-on-insulator (SOI) die may include a silicon layer including a first side and a second side, and an insulative layer coupled directly to the second side of the silicon layer. The insulative layer may not be coupled to any other silicon layer.

20 Claims, 3 Drawing Sheets



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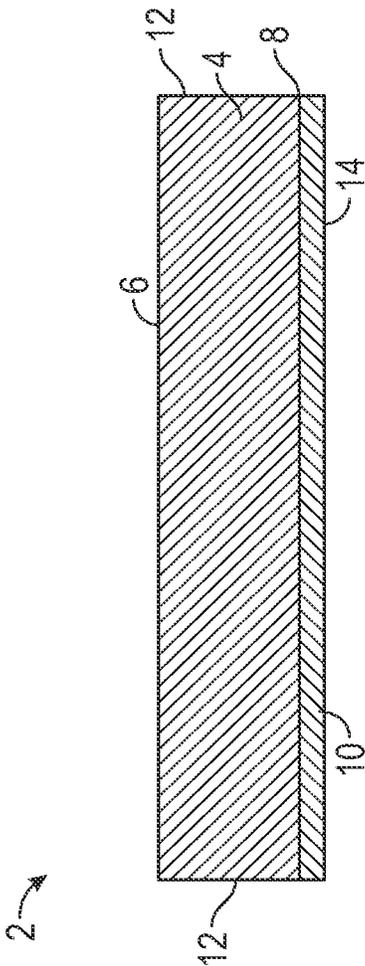


FIG. 1

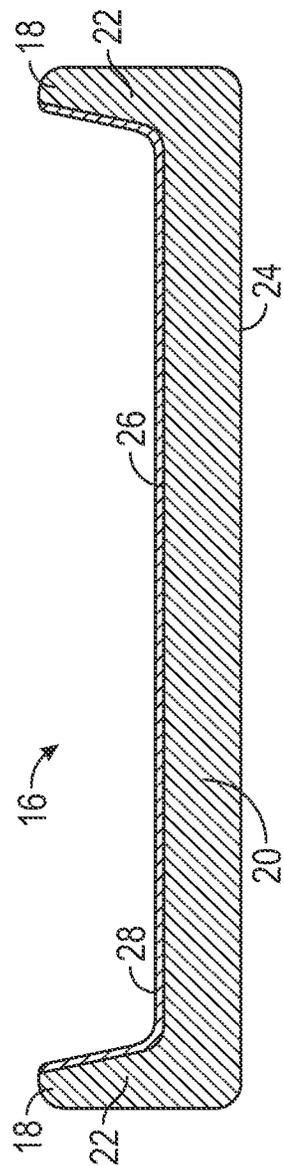
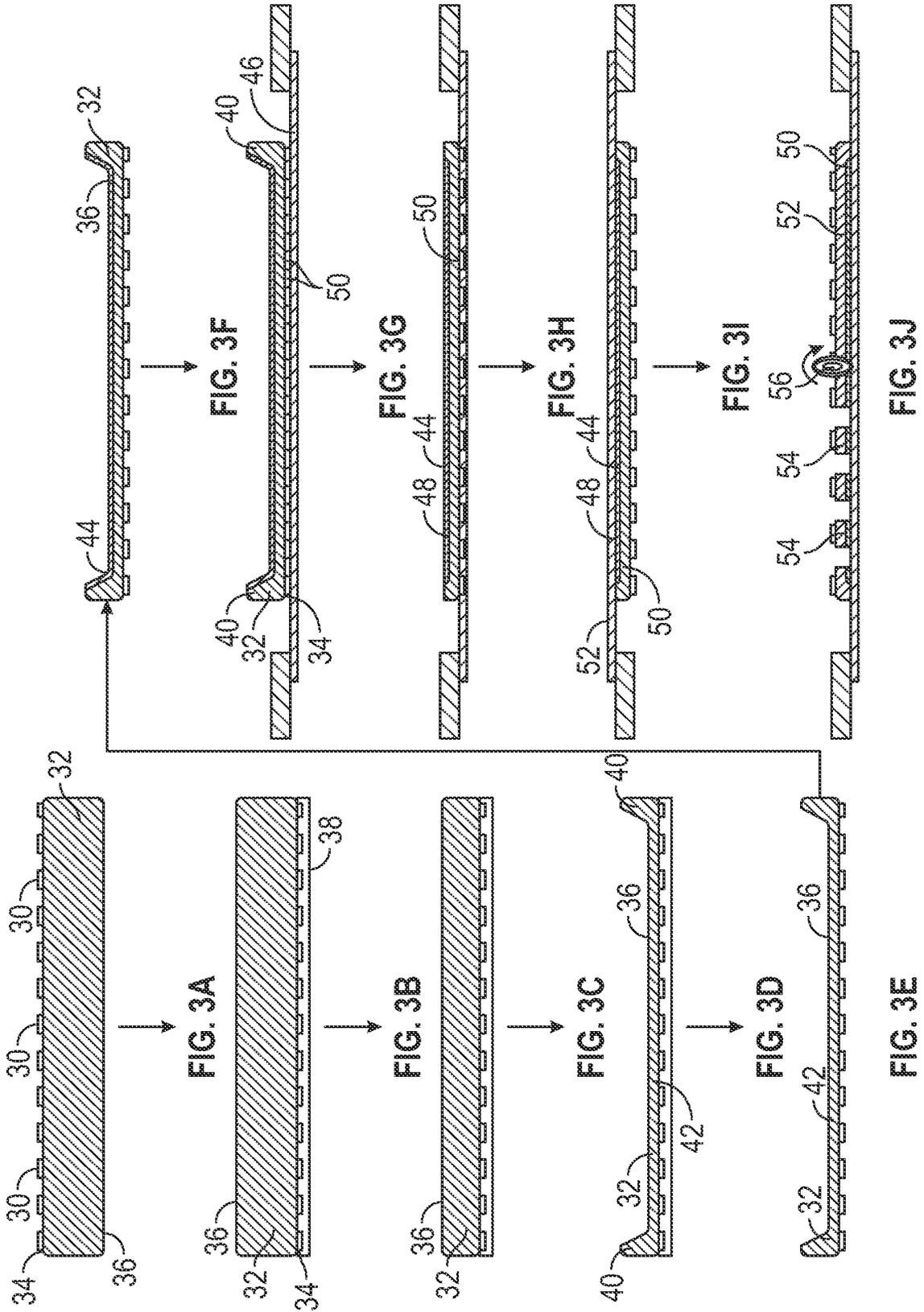


FIG. 2



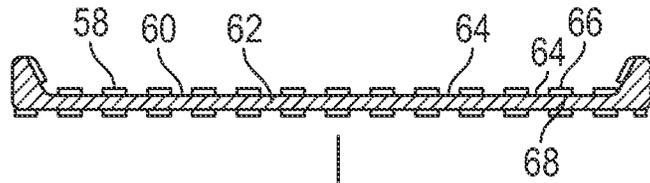


FIG. 4A

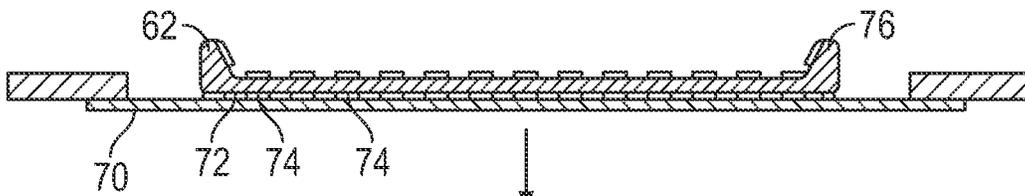


FIG. 4B

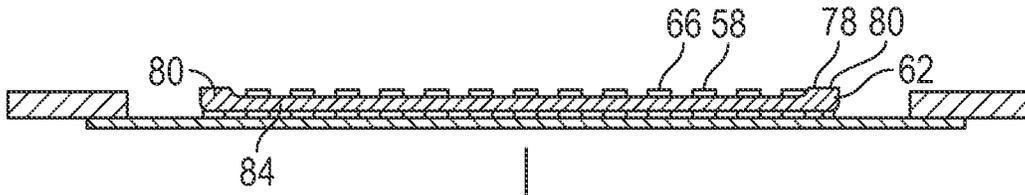


FIG. 4C

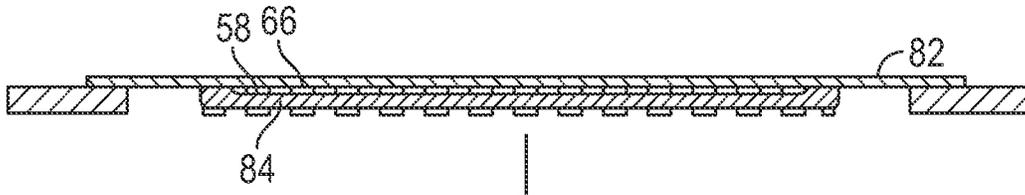


FIG. 4D

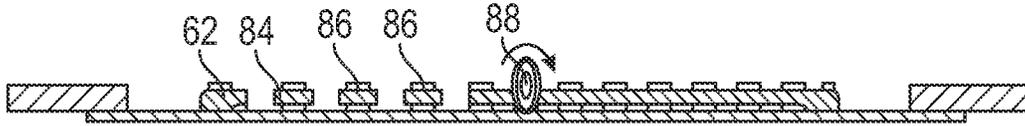


FIG. 4E

SOI SUBSTRATE AND RELATED METHODSCROSS REFERENCE TO RELATED
APPLICATIONS

This application is a continuation application of the earlier U.S. Utility Patent Application to Seddon et al., entitled, "SOI Substrate and Related Methods," application Ser. No. 17/937,918, filed Oct. 4, 2022, now pending, which application is a continuation application of the earlier U.S. Utility Patent Application to Seddon et al., entitled, "SOI Substrate and Related Methods," now issued as U.S. Pat. No. 11,495,529, which application is a divisional application of the earlier U.S. Utility Patent Application to Seddon et al., entitled, "SOI Substrate and Related Methods," now issued as U.S. Pat. No. 10,741,487, the disclosures of each of which are hereby incorporated entirely herein by reference.

BACKGROUND

1. Technical Field

Aspects of this document relate generally to semiconductor substrates. More specific implementations involve silicon-on-insulator (SOI) substrates.

2. Background

Silicon-on-insulator (SOI) substrates include a silicon junction above an electrical insulator. SOI substrates have been used to reduce capacitance.

SUMMARY

Implementations of a silicon-on-insulator (SOI) die may include a silicon layer including a first side and a second side, and an insulative layer coupled directly to the second side of the silicon layer. The insulative layer may not be coupled to any other silicon layer.

Implementations of an SOI die may include one, all, or any of the following:

The SOI die may include a plurality of semiconductor devices on the first side of the silicon layer.

The SOI die may include a conductive layer coupled directly to the second side of the silicon layer.

The silicon layer may be less than 35 micrometers (um) thick.

The insulative layer may include a thermally conductive material.

Implementations of methods of making an SOI die may include forming a ring around the perimeter of a second side of a silicon substrate through backgrinding the second side of the substrate to a desired substrate thickness, depositing an insulative layer onto the second side of the silicon substrate after backgrinding, removing the ring around the perimeter of the second side of the silicon substrate, and singulating the silicon substrate into a plurality of SOI die.

Implementations of methods of making an SOI die may include one, all, or any of the following:

The method may include forming a plurality of semiconductor devices on the first side of the silicon substrate, the first side opposite the second side of the silicon substrate.

The plurality of silicon die may be less than 35 um thick.

The method may further include stress relief etching the second side of the silicon substrate.

The insulative layer may be deposited using either co-evaporation or co-sputtering.

The method may further include dissipating heat through a heat dissipation device during deposition of the insulative layer.

The co-evaporation or co-sputtering may occur at temperatures that do not require heat dissipation.

The method may not include implanting hydrogen.

No sacrificial carrier substrate may be used in the method.

Implementations of methods of making an SOI die may include forming a ring around the perimeter of a second side of a silicon substrate through backgrinding the second side of the silicon substrate to a desired substrate thickness, depositing a conductive layer onto the second side of the silicon substrate, depositing an insulative layer over the conductive layer, removing the ring around the perimeter of the second side of the silicon substrate, and singulating the silicon substrate into a plurality of SOI die.

Implementations of methods of making an SOI die may include one, all, or any of the following:

The method may further include patterning the conductive layer.

The conductive layer may include titanium.

The silicon substrate may be thinned to less than 35 um.

The insulative layer may be deposited using either co-evaporation or co-sputtering.

Implementations of a silicon-on-insulator (SOI) die may only include a silicon layer including a first side and a second side, a semiconductor device coupled to the first side of the silicon layer, and an insulative layer coupled directly to the second side of the silicon layer. The insulative layer may not be coupled to any other silicon layer.

The foregoing and other aspects, features, and advantages will be apparent to those artisans of ordinary skill in the art from the DESCRIPTION and DRAWINGS, and from the CLAIMS.

BRIEF DESCRIPTION OF THE DRAWINGS

Implementations will hereinafter be described in conjunction with the appended drawings, where like designations denote like elements, and:

FIG. 1 is a cross sectional side view of a silicon-on-insulator (SOI) die;

FIG. 2 is a cross sectional side view of an SOI substrate with a ring formed around the perimeter thereof;

FIGS. 3A-3J are cross sectional side views of an implementation of a method of forming an SOI die; and

FIGS. 4A-4E are cross sectional side views of a second implementation of a method of forming an SOI die.

DESCRIPTION

This disclosure, its aspects and implementations, are not limited to the specific components, assembly procedures or method elements disclosed herein. Many additional components, assembly procedures and/or method elements known in the art consistent with the intended silicon-on-insulator (SOI) substrates and die will become apparent for use with particular implementations from this disclosure. Accordingly, for example, although particular implementations are disclosed, such implementations and implementing components may comprise any shape, size, style, type, model, version, measurement, concentration, material, quantity, method element, step, and/or the like as is known in the art for such SOI substrates and die, and implementing components and methods, consistent with the intended operation and methods.

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Referring to FIG. 1, a cross sectional side view of an SOI die is illustrated. The SOI die 2 includes a silicon layer 4. The silicon layer 4 includes a first side 6 and a second side 8 opposite the first side. In various implementations, the silicon layer 4 may be, by non-limiting example, an epitaxial silicon layer, a polysilicon layer, a single crystal silicon layer, any combination thereof, or any other silicon-containing layer material. In other implementations, it is understood that a layer other than a silicon-containing layer may be used, such as, by non-limiting example, gallium arsenide, silicon carbide, or a metal-containing layer. While this disclosure primarily refers to silicon and SOI die, it is understood that the principles disclosed herein may be applied to other non-silicon containing die. In various implementations, one or more semiconductor devices may be coupled to the first side 6 of the silicon layer. In such implementations, the one or more semiconductor devices may include high voltage junction devices or power management devices, while in other implementations the one or more semiconductor devices may include other types of semiconductor devices.

In various implementations, the silicon layer 4 may be less than 35 micrometers (microns, μm) thick. In other implementations, it may be 35 or more μm thick. In particular implementations, the silicon layer 4 may be as thin as about 8 μm thick. In implementations where the silicon layer 4 is to be used in medium voltage applications [100 volts (V) or 2 amps (A)], the silicon layer may be about 20-30 μm thick. In other implementations where the silicon layer 4 is to be used in high voltage applications (1 kV, 10 A), the silicon layer may be greater than 100 μm thick.

The SOI die also includes an insulative layer 10 coupled to the second side 8 of the layer 4. In various implementations, the insulative layer 10 may be coupled directly to the second side 8 of the layer 4. The insulative layer may include any electrical insulator, and in particular implementations, may include an electrical insulator which is thermally conductive. In particular implementations, the insulative layer may include, by non-limiting example, BN, AlN, AlO_x , TiO_x , TiN_x , SiO_2 , sapphire (alpha- Al_2O_3), Mica, Ta_2O_5 , diamond, Si_xN_y , SiC, GaN, graphene oxide, nanocomposite silicates, silicon rubber, a graphite polymer matrix, tungsten carbide, any other electrically insulative material, or any combination thereof. In implementations where the SOI die 2 is to be used in medium voltage applications [100 volts (V) or 2 amps], the insulative layer may be about 2,000-5,000 Angstroms (Å) thick. In other implementations where the SOI die 2 is to be used in high voltage applications (1 kV, 10 amps), the insulative layer may be about 1 μm thick. In other implementations, the insulative layer may be less than 2 kÅ thick or more than 1 μm thick. In particular implementations, the thickness of the insulative layer may be 3 μm or more thick.

In various implementations, and as illustrated by FIG. 1, the sidewalls of the insulative layer 10 may be a continuous layer coextensive with the sidewalls 12 of the silicon layer 4. In other implementations, the insulative layer 10 may be patterned. Though not illustrated by FIG. 1, in various implementations the SOI die 2 may include a conductive layer directly coupled to the second side 8 of the layer 4. In particular implementations, the conductive layer may be between the layer 4 and the insulative layer 10. In implementations where the insulative layer 10 is patterned, the conductive layer may fill the recesses in the insulative layer. The conductive layer may also be patterned. In implementations including a conductive layer, the conductive layer

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may include titanium, aluminum, copper, gold, silver nickel, any other metal, any alloy thereof, or any combination thereof.

In various implementations, the insulative layer 10 is not coupled to any other layer or silicon layer aside from the silicon layer 4. While various implementations of SOI die include a layer of silicon over an insulative layer over a second layer of silicon (or at least a portion of a second layer of silicon), the implementations of the SOI die disclosed herein may only include a single silicon layer. In such implementations, this may allow for the second side 14 of the insulative layer 10 to be fully exposed. In particular implementations, the SOI die may only include a silicon layer 4 having a first side 6 and a second side 8 and an insulative layer 10 directly coupled to the second side 8 of the silicon layer 4. The insulative layer 10 may be patterned in various implementations. In other implementations, the SOI die may only include a silicon layer having a first side and a second side, a semiconductor device coupled to or formed on/in the first side of the silicon layer, and an insulative layer coupled directly to the second side of the silicon layer. In still other implementations, the SOI die may only include a silicon layer having a first side and a second side, an insulative layer coupled to the second side of the silicon layer, and a conductive layer directly coupled to the second side of the silicon layer as well as the insulative layer.

Referring to FIG. 2, a cross sectional side view of an SOI substrate with a ring formed around the perimeter thereof is illustrated. In various implementations, the substrate 16 illustrated by FIG. 2 may be formed prior to forming the SOI die 2 illustrated by FIG. 1. The SOI substrate 16 includes a substrate 18 having a first side 24 and a second side 26. The substrate 18 may be, by non-limiting example, an epitaxial silicon substrate, a polysilicon substrate, single crystal silicon substrate, any combination thereof, or any other silicon-containing substrate material. In other implementations, it is understood that a substrate other than a silicon-containing substrate may be used, such as, by non-limiting example, gallium arsenide, silicon carbide, or a metal-containing substrate. While this disclosure primarily refers to silicon and SOI substrates, it is understood that the principles disclosed herein may be applied to other non-silicon containing substrates. As illustrated by FIG. 2, the substrate 18 includes a thinned portion 20 and a ring 22 extending around the perimeter of the substrate. The ring may result from backgrinding in a process marketed under the trade name TAIKO by DISCO of Tokyo, Japan. The thinned portion 20 of the substrate 18 may be less than 35 micrometers (μm) thick. In other implementations, it may be 35 or more μm thick. In particular implementations, the thinned portion 20 of the substrate 18 may be as thin as about 8 μm thick. In other particular implementations, the thinned portion 20 of the substrate may be about 20-30 μm thick.

The SOI substrate 16 includes an insulative layer 28 coupled to the second side 26 of the substrate 18. In various implementations, the insulative layer 28 may be coupled directly to the second side 26 of the substrate 18. The insulative layer may include any electrical insulator, and in particular implementations, may include an electrical insulator which is thermally conductive. In particular implementations, the insulative layer may include, by non-limiting example, BN, AlN, AlO_x , TiO_x , TiN_x , SiO_2 , sapphire (alpha- Al_2O_3), Mica, Ta_2O_5 , diamond, Si_xN_y , SiC, GaN, graphene oxide, nanocomposite silicates, silicon rubber, a graphite polymer matrix, tungsten carbide, any other electrically insulative material, or any combination thereof. In various implementations, the insulative layer 28 may be about

2,000-5,000 Angstroms (Å) thick. In other implementations, the insulative layer **28** may be about 1 μm thick. In still other implementations, the insulative layer **28** may be less than 2 kÅ thick, more than 1 μm thick, or between 2 kÅ and 1 μm thick. In particular implementations, the insulative layer may be 3 μm or more than 3 μm thick. In various implementations, and as illustrated by FIG. 2, the insulative layer **28** may be a solid and continuous layer covering the second side **26** of the substrate **18**. In other implementations, the insulative layer **28** may be patterned. In various implementations, the insulative layer **28** is not coupled to any other substrate aside from the substrate **18**.

In various implementations, the SOI substrate **16** may also include a conductive layer coupled to the insulative layer **28** and to the second side **26** of the substrate **18** (not illustrated in FIG. 2). In various implementations, the conductive layer may be directly coupled to the second side **26** of the substrate **18**. In particular implementations, the conductive layer may be between the substrate **18** and the insulative layer **28**. In implementations including a conductive layer, the conductive layer may any type of material previously disclosed herein and may or may not be patterned.

Referring to FIGS. 3A-3J, cross sectional side views of a substrate at various points of a method for forming an SOI die is illustrated. Referring specifically to FIG. 3A, the method for forming an SOI die may include forming a plurality of semiconductor devices **30** on, or coupling a plurality of semiconductor devices **30** to, a first side **34** of a substrate **32**. While FIGS. 3A-3J indicate that the plurality of semiconductor devices **30** are formed on the substrate **32** before thinning the substrate and/or before applying an insulative layer, in other implementations, the plurality of semiconductor devices may be formed on the substrate after thinning the substrate and/or after applying an insulative layer to the substrate. The plurality of semiconductor devices may be any type of semiconductor device disclosed herein.

Referring to FIG. 3B, the method for forming an SOI die may include applying backgrind tape **38** to the first side **34** of the substrate **32**. Referring to FIG. 3C, the method may also include initially thinning the substrate **42**. In various implementations, the substrate may be initially thinned to about 355 μm, though in other implementations the substrate may be thinned to more or less than this thickness. The substrate **32** may be thinned through backgrinding, etching, or any other thinning technique.

Referring to FIG. 3D, the method for forming an SOI die includes forming a ring **40** around the perimeter of a second side **36** of a substrate **32** through backgrinding the second side of the substrate **32** to a desired substrate thickness. In particular implementations, the backgrinding may use a process marketed under the trade name TAIKO by DISCO Corporation of Tokyo, Japan. The backgrinding leaves a ring of non-removed material (TAIKO ring) along the perimeter of the second side **36** of the substrate **32** which helps to prevent the substrate from curling, warping or otherwise bending during further processing while at the same time removing most of the thickness and material of the second side **36** of the substrate **32**. The ring **40** may also offer sufficient stress management for the insulative layer applied to the substrate as described later herein. In other implementations of methods of forming semiconductor devices the TAIKO process may not be used, but another backgrinding or other material-removal technique may be used, such as removing the material through a wet etch. In various implementations, the thinned portion **42** of the substrate **32**

may be 50 μm thick. In other implementations, it may be more or less than 50 μm thick, including any die or substrate thickness previously disclosed herein.

Referring to FIG. 3E, the method for forming an SOI die may include etching the second side **36** of the substrate **32**, or the thinned portion **42**. In particular implementations, the etching may be stress relief etching. This stress relief etching may be used to obtain the final desired thickness of the wafer. The stress relief etching may include wet chemical etching. In other implementations, it may include dry etching or polishing instead of wet chemical etching, however, wet chemical etching may result in a cleaner substrate with less residual particles. Acid may be used to etch the substrate, and in various implementations may include, by non-limiting example, hydrofluoric acid, acetic acid, nitric acid, and any other acid or combination thereof. The wet chemical etch may be tightly monitored and controlled so that the targeted thickness of the wafer is achieved. In various implementations, the second side **36** of the substrate **32** may be etched until the thinned portion **42** of the substrate is 25 μm thick. In other implementations, the substrate **32** may be etched until thinned portion **42** is more or less than 25 μm thick. In implementations where the substrate is wet etched, the wet etch may prepare the substrate to better adhere to later deposited materials and/or devices. In various implementations, the backgrind tape **38** may be removed.

Referring to FIG. 3F, the method for forming an SOI die includes depositing an insulative layer **44** onto the second side **36** of the substrate **32** after backgrinding. In various implementations, the insulative layer **44** may be deposited at a low temperature. The low temperature deposition may allow for the insulative layer to be deposited without overheating the substrate, especially in instances where the substrate has been thinned. The substrate **32** may have a low thermal resistance. In various implementations, the insulative layer may be deposited through spin-on techniques, chemical vapor deposition (CVD), sputtering, evaporation, co-sputtering, or co-evaporation, and in particular implementations, may be deposited at a temperature that does not require heat dissipation. In implementations where the insulative layer is deposited using either co-sputtering or co-evaporation, the overall performance of the SOI die and the adhesion of the insulative layer **44** to the substrate **32** may be improved. In various implementations, however, the method may include dissipating heat through a heat dissipation device during deposition of the insulative layer **44**. The heat dissipation device may include, among other devices, cooling chucks or common evaporators. The insulative layer **44** may be any insulative material previously disclosed herein, and may be applied in any thickness previously disclosed herein. In the implementation illustrated by FIG. 3F, the method includes depositing the insulative layer **44** directly to the second side **36** of the substrate **32**. In other implementations, the method may include directly depositing a conductive layer to the second side of the substrate prior to deposition of the insulative layer. The conductive layer may enhance the adhesion between the insulative layer and the substrate as well as provide potential electrical contacts on the substrate. In such implementations, the conductive layer may include any electrically conductive material disclosed herein. In various implementations, the conductive layer may be deposited through, by non-limiting example, sputtering, evaporation, electroplating, any other deposition technique, or any combination thereof.

Referring to FIG. 3G, the method for forming an SOI die includes mounting the substrate **32** to a film frame. The first side **34** and/or the plurality of semiconductor devices **30** may be directly coupled to the film frame **46**. Referring to FIG. 3H, the method may include removing the ring **40**. The ring may be removed through grinding the ring portion of the substrate. In other implementations, the ring may be removed through plasma etching or cutting the ring from the remaining substrate using, by non-limiting example, a laser or a saw. In various implementations, the ring is removed to the extent that the backside **48** of the SOI substrate **50** opposite the side of the SOI substrate coupled to the film frame is substantially level.

Referring to FIG. 3I, the method for forming an SOI die includes applying a final dicing tape **52** to the backside **48** of the SOI substrate **50**, or to the insulative layer **44**. In such implementations, the method may also include removing the exposed tape used to couple the substrate **32** to the film frame explained in FIG. 3G. In other implementations, rather than applying the final dicing tape, the SOI substrate may be flipped so the insulative layer **44** is directly coupled to the existing tape.

Referring to FIG. 3J, the method for forming an SOI die may include singulating the substrate **32** (and the SOI substrate **50**) into a plurality of SOI die **54**. The SOI substrate may be singulated through, by non-limiting example, a saw **56**, a laser, plasma etching, or any other singulation device or method. In various implementations, the SOI die may be coupled to an interposer after singulation.

Referring to FIGS. 4A-4E, cross sectional side views of a second implementation of a method for forming an SOI die are illustrated. Referring specifically to FIG. 4A, the method may include patterning an insulative layer **58** coupled to a second side **60** of a substrate **62**. As illustrated, the substrate **62** has been thinned to form a ring using any of the thinning methods disclosed in this document. In such implementations, the method includes masking the insulative layer and removing portions of the insulative layer where the mask pattern is absent. The SOI substrate **64** may be the same as or similar to the SOI substrate illustrated in FIG. 3F with the exception that the insulative layer **58** is patterned. The process used to produce the SOI substrate illustrated by and described in relation to FIG. 3F may also be used in making the SOI substrate with the patterned insulative layer illustrated in FIG. 4A.

In the implementation illustrated by FIG. 4A, the method includes depositing the insulative layer **58** directly onto the second side **60** of the substrate **62**. In other implementations, the method may include directly depositing a conductive layer onto the second side of the substrate prior to deposition of the insulative layer. The conductive layer may enhance the adhesion between the insulative layer and the substrate as well as provide potential electrical contacts on the substrate. The conductive layer may be patterned. In still other implementations, the conductive layer may be deposited within recesses **64** formed in the patterned insulative layer **58**. The conductive layer may also cover all of or a portion of a second side **66** of the insulative layer **58** opposite the first side **68** of the insulative layer. The conductive layer may include any conductive material disclosed herein. In various implementations, the conductive layer may be deposited through, by non-limiting example, sputtering, evaporation, electroplating, any other deposition technique, or any combination thereof.

Referring to FIG. 4B, implementations of a method for forming an SOI die includes mounting the substrate **62** to a

film frame **70**. The first side **72** and/or the plurality of semiconductor devices **74** may be directly coupled to the film frame **70**. Referring to FIG. 4C, the method may include removing the ring **76**. The ring **76** may be removed through grinding the ring portion of the substrate or any other method disclosed in this document. In various implementations, the ring is removed to the extent that the second side **78** of the substrate **62** on the ends **80** of the substrate are substantially level with the second side **66** of the insulative layer **58**.

Referring to FIG. 4D, the method for forming an SOI die may include applying a final dicing tape **82** to the second side **66** of the insulative layer **58**. In such implementations, the method may also include removing the exposed tape used to couple the substrate **62** to the film frame **70** as explained in relation to FIG. 4B. In other implementations, rather than applying the final dicing tape, the SOI substrate **84** may be flipped so the insulative layer **58** is directly coupled to the existing tape.

Referring to FIG. 4E, the method for forming an SOI die includes singulating the substrate **62** (and the SOI substrate **84**) into a plurality of SOI die **86**. The SOI substrate **84** may be singulated through, by non-limiting example, a saw **88**, a laser, plasma etching, or any other singulation device or method. In various implementations, the SOI die may be coupled to an interposer after singulation.

The implementations of SOI substrates and SOI die disclosed herein may be formed without using a process that implants hydrogen within a substrate, without forming bubbles within the substrate, without breaking the substrate, and/or without having to polish the substrate. Further, the method may be performed without using a sacrificial carrier substrate and without having to cut, grind, or otherwise remove the sacrificial carrier substrate. The methods of forming such implementations of SOI die may have sufficient stress management of the backside insulating material to be able to form an SOI die without a sacrificial carrier substrate while still having a thin silicon layer coupled to the insulative layer. In this way, no remaining carrier material may be present in the resulting SOI die.

In places where the description above refers to particular implementations of SOI substrates/die implementing components, sub-components, methods and sub-methods, it should be readily apparent that a number of modifications may be made without departing from the spirit thereof and that these implementations, implementing components, sub-components, methods and sub-methods may be applied to other SOI substrates/die.

What is claimed is:

1. A method of making a silicon-on-insulator (SOI) die, the method comprising:

depositing an insulative layer directly to a second side of a silicon substrate, the silicon substrate comprising a first side and the second side; and
singulating the silicon substrate into a plurality of SOI die;
wherein the insulative layer is coupled to silicon only through the second side of the silicon substrate; and
wherein the insulative layer comprises an insulative material that fills an entire area within an outer perimeter of the insulative layer.

2. The method of claim 1, further comprising forming one or more semiconductor devices on the first side of the silicon substrate.

3. The method of claim 1, wherein the insulative layer comprises a thermally conductive material.

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- 4. The method of claim 1, wherein the silicon substrate comprises no bubbles therein.
- 5. The method of claim 1, wherein the silicon substrate comprises no implanted gas therein.
- 6. The method of claim 1, wherein the silicon substrate is between 20-30 microns thick.
- 7. The method of claim 1, wherein the insulative layer is between 2,000-5,000 angstroms thick.
- 8. A method of making a silicon-on-insulator (SOI) die, the method comprising:
 - depositing an insulative layer directly to a second side of a silicon substrate, the silicon substrate comprising a first side and the second side;
 - backgrinding the silicon substrate to a thickness less than 35 micrometers thick; and
 - singulating the silicon substrate into a plurality of SOI die;
 - wherein the insulative layer is coupled to silicon only through the second side of the silicon substrate; and
 - wherein an outer perimeter of the silicon substrate is larger than an outer perimeter of the insulative layer.
- 9. The method of claim 8, further comprising forming one or more semiconductor devices on the first side of the silicon substrate.
- 10. The method of claim 8, wherein the insulative layer comprises a thermally conductive material.
- 11. The method of claim 8, wherein the silicon substrate comprises no bubbles therein.
- 12. The method of claim 8, wherein the method does not comprise implanting hydrogen.

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- 13. The method of claim 8, wherein the silicon substrate is thinned between 20-30 microns thick.
- 14. A method of making a silicon-on-insulator (SOI) die, the method comprising:
 - depositing a conductive layer onto a second side of a silicon substrate, the silicon substrate comprising a first side and the second side;
 - depositing an insulative layer over the conductive layer; and
 - singulating the silicon substrate into a plurality of SOI die;
 - wherein the insulative layer is coupled to silicon only through the second side of the silicon substrate; and
 - wherein an outer perimeter of the silicon substrate is larger than an outer perimeter of the insulative layer.
- 15. The method of claim 14, further comprising backgrinding the silicon substrate to a thickness less than 35 micrometers thick.
- 16. The method of claim 14, further comprising patterning the conductive layer.
- 17. The method of claim 14, wherein the silicon substrate comprises no bubbles therein.
- 18. The method of claim 14, wherein the insulative layer is not coupled to any other silicon substrate.
- 19. The method of claim 14, wherein the conductive layer comprises titanium.
- 20. The method of claim 14, further comprising forming one or more semiconductor devices on the first side of the silicon substrate.

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